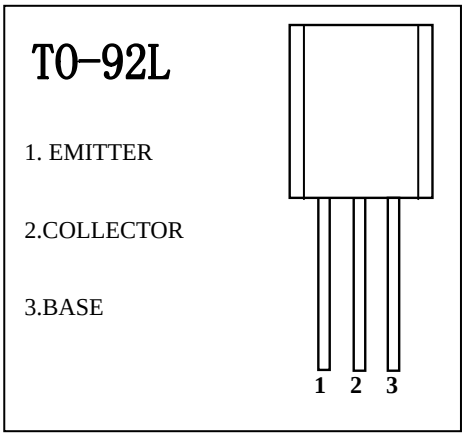
深圳市晶泰源电子有限公司

2SD468 TRANSISTOR(NPN)



FEATURES

- Excellent linearity or Current Gain
- Low saturation voltage
- Complementary to 2SB562

MAXIMUM RATINGS(TA=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	ColleatorBase Voltage	25	V
VCEO	ColleatorEmitter Voltage	20	V
VEBO	EmitterBase Voltage	5	V
IC	Colleator CurrentContinuous	1.0	A
PC	Coueator Power Dissipature	0.75	W
TJ	Junction Temperature	150	℃
Tatg	Storage Temperature	55150	℃

ELECTRICAL CHARACTERISTICS(Tamb=25℃ unless otherwise specjfied):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collectorbase breakdown voltage	$V_{(BR)CBO}$	I_C=1mA, I_E=0	25			V
Collectoremittre breakdown’ voltage	$V_{(BR)CEO}$	I_C=1mA, I_B=0	20			V
Emitterbase breakdown voltage	$V_{(BR)EBO}$	I_C=1mA, I_C=0	5			V
Collector cutoff current	I_{CBO}	V_{CB}=25V, I_E=0			0.5	μA
Collector cutoff current	I_{CEO}	Vce=20V, I_B=0			1.0	μA
Emitter cutoff current	I_{EBO}	V_{EB}=5V, I_C=0			0.1	μA
DC current gain	H_{FE}	Vce=5V, Ic=1mA	85		240	
Collectoremittre saturation voltage	VCE(sat)	I_C=800mA, I_B=80mA			0.5	V
Baseemittre saturation voltage	VBE(sat)	I_C=800mA, I_B=80mA			1.2	V
Gain Bandwidth Product	fT	V_{CE}=2V, I_C=500mAz		190		MHz

深圳市晶泰源电子有限公司
电话：0755-83211536 传真：0755-83206326
深圳市福田区华强北路华强广场C座11C